



SUBJECT AREAS:

TOPOLOGICAL
INSULATORS

QUANTUM HALL

ELECTRONIC PROPERTIES AND
MATERIALS

ERRATUM: Quantum Anomalous Hall Effect and Tunable Topological States in 3d Transition Metals Doped Silicene

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This Article contains typographical errors in equations in the Results section “Topological states from Chern number analysis”. In these equations “:” should read “ \otimes ”.

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“ $\{A, B\} : \{\uparrow, \downarrow\}$ ” should read “ $\{A, B\} \otimes \{\uparrow, \downarrow\}$ ”

Equation 2 should read:

$$H_s^\pm = \varepsilon_{eff} \tau_0 \otimes \sigma_0 \pm \tau_3 \otimes h_{11} + \hbar v_F (\kappa_x \tau_1 \mp \kappa_y \tau_2) \otimes \sigma_0,$$

Equation 3 should read:

$$H_d^\pm = \lambda_R^{ext} (\pm \tau_1 \otimes \sigma_2 - \tau_2 \otimes \sigma_1) + \Delta \tau_3 \otimes \sigma_0 + M \tau_0 \otimes \sigma_3,$$

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